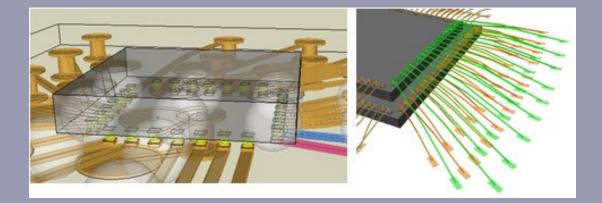
tegrated Circuits packaging





PH-ESE Seminar

David Porret PH/ESE/ME – 7/6/2011

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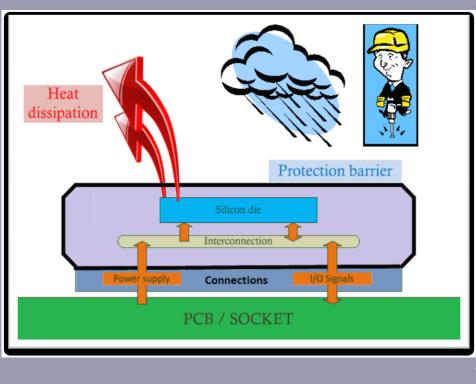
- Introduction to the IC packaging world
- Packaging families
 - Hybrids
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 - Multi-chip Modules (MCM)
 - System in Package (SiP)
- Technical aspects
 - Temperature
 - Enclosures Encapsulation
 - Electrical interconnections
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IC Packaging

"Everything in electronics between the chip and the system"



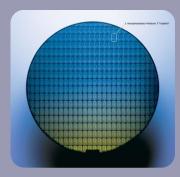
IMAPS (International Microelectronics And Packaging Society)



Package specifications Electrical (optical sometimes) : Carry clean signals from/to the dies(s). Shielding if it's a concern (IC-EMC). Thermal : Evacuate the heat, avoid hot-spots. Mechanical : Physical protection against shocks, dust, water. Easy handling, small and light. Manufacturing : Modularity, design reuse.

- Reliability, cost.
- Compatibility with contractors workshop.

Packaging world



Front-end

- Wafer Level Package (WLP)
- Trough-Silicon-Via (TSV)
- MEMS packaging



Contraction of the second seco

Back-end

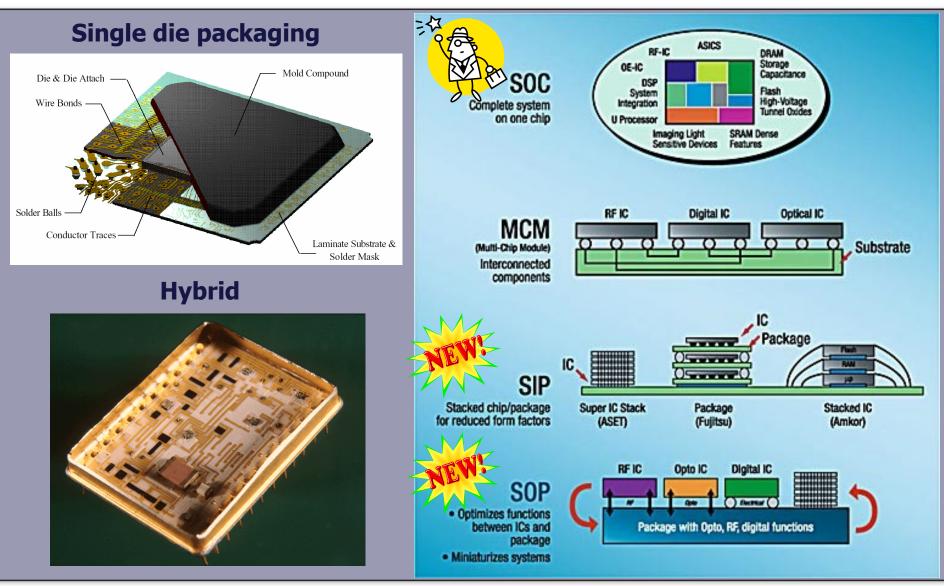
- High-density PCB
- Wire bonding
- Flex
- Hybrids

The big packaging companies:

- AMKOR (USA)
- ASE Global (Taiwan)
- STATS ChipPAC (Singapore)
- SPIL (Taiwan)

Introduction to the packaging world

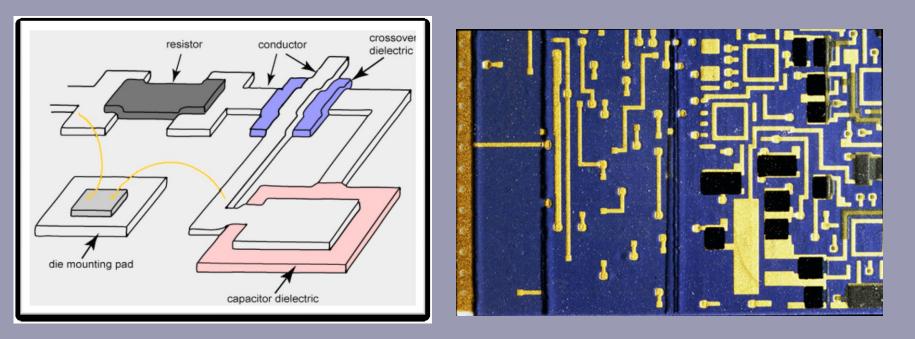
New concepts for smaller/faster/cheaper



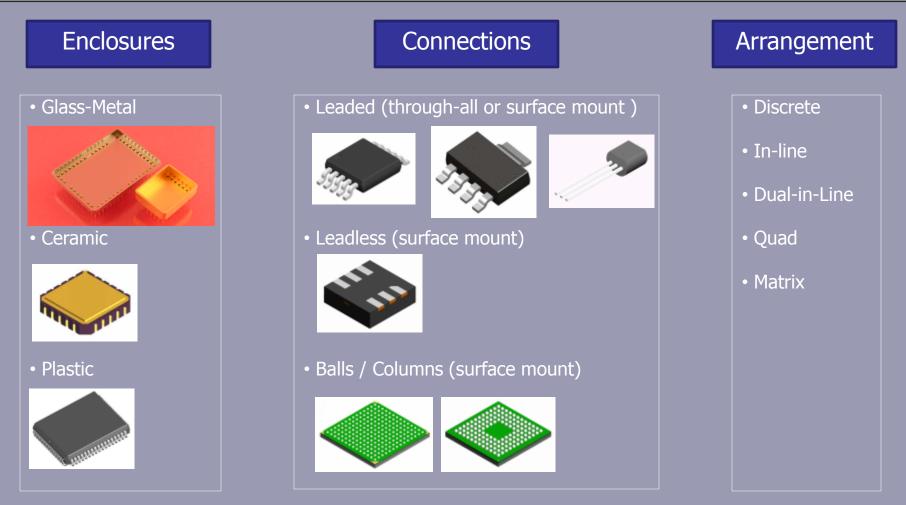
Packaging families

Hybrids

- Mature technology
- Built on ceramic, glass, metal.
- Chips are bonded directly on the substrate.
- Passives are printed + "fired" (thick-film) or deposited (thin-film) on the substrate. Precise values achieved by laser trimming.

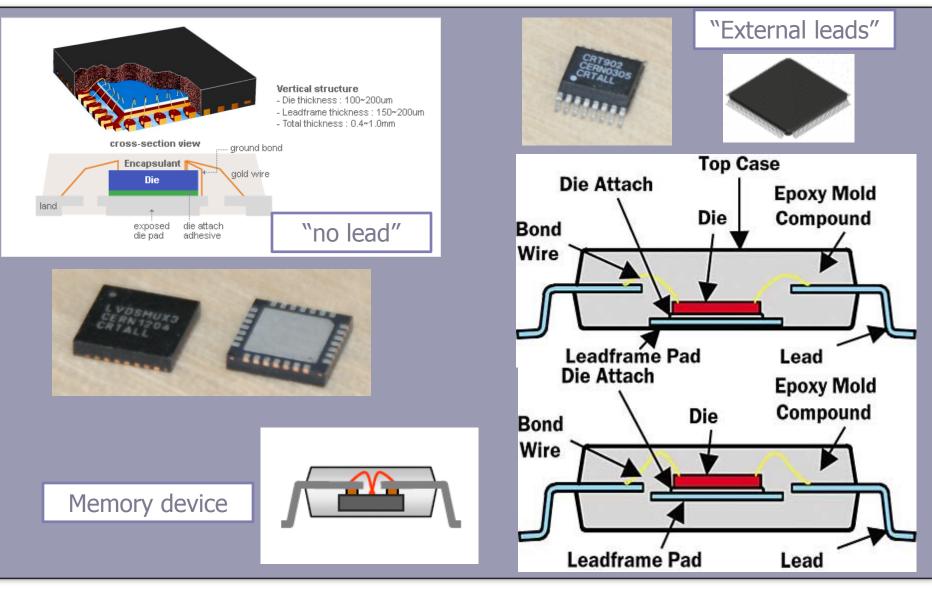


Standard packages formats

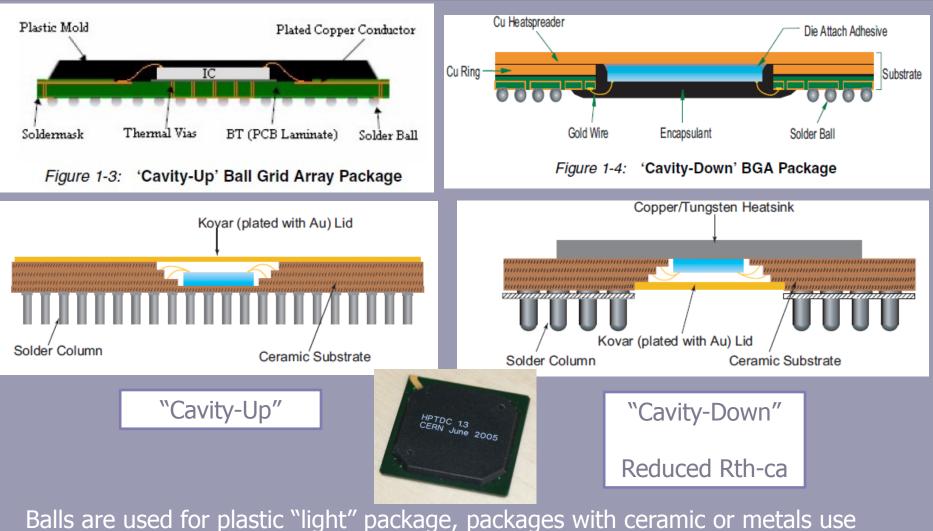


Each package has to be selected according to some specifications and assembly capabilities.

Standard packages details : Lead frame

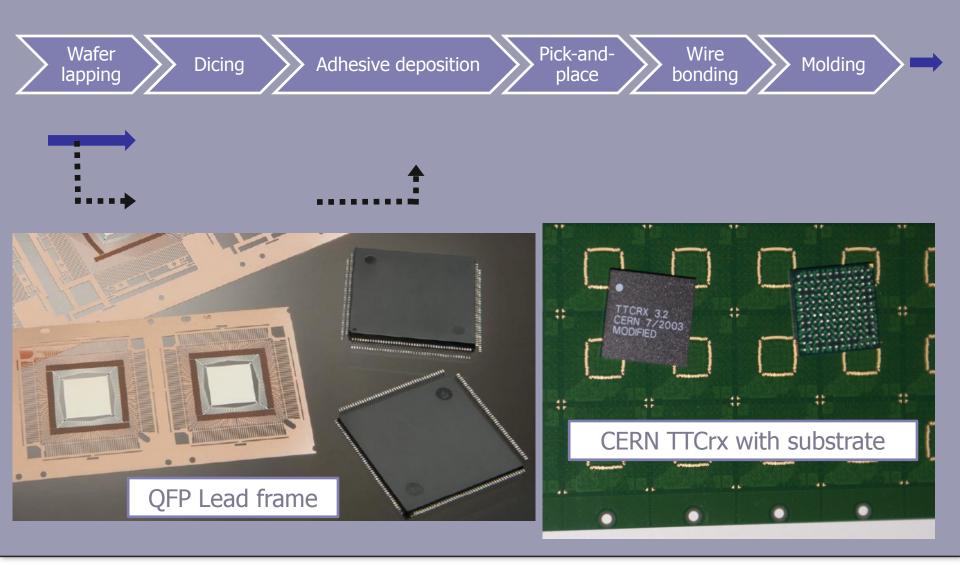


Standard packages details: balls + bonding

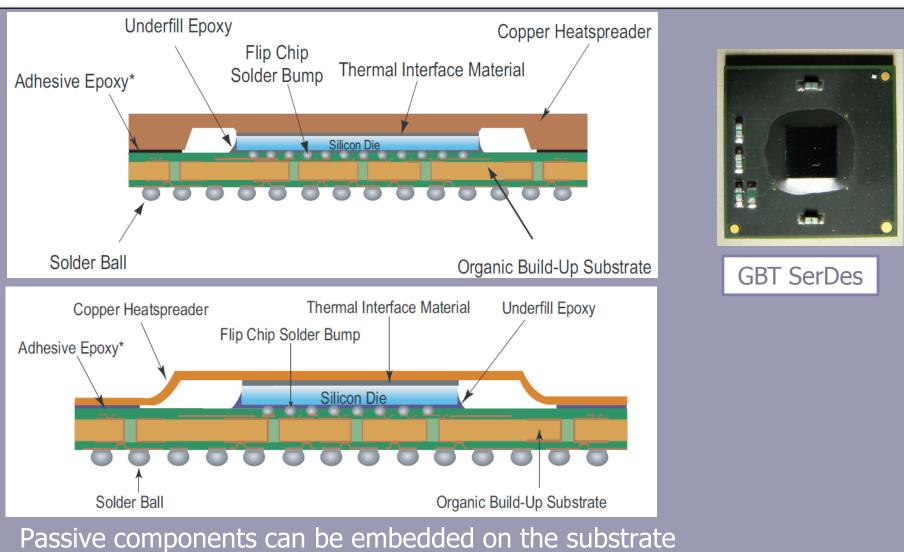


hard balls or columns.

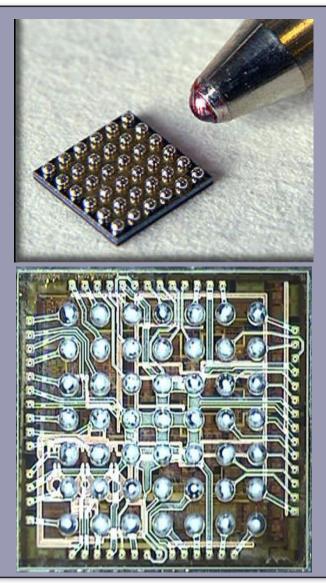
Package with wire bonding :process



Standard packages details: balls + flip-chip

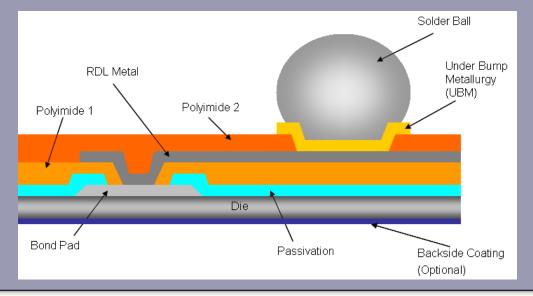


Wafer Level Package (WLP)



• Front-end process

- Small and low-cost for big volumes
- Good electrical performances
- Fine pitch PCB required
- Signals fan-out with RDL (re-distribution layer)



WLP process

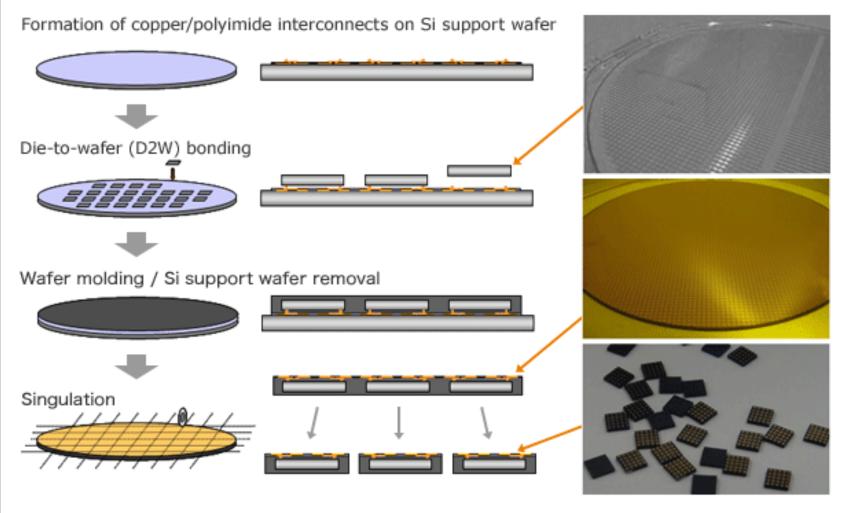
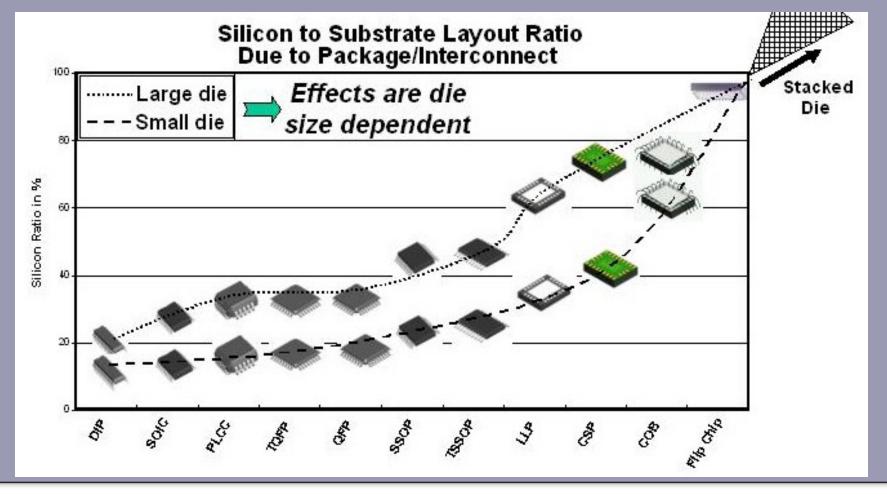


Figure 1 FO-WLP/SiWLP Production Process

Chip Scale Package (CSP)

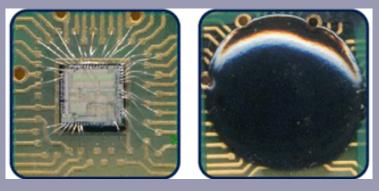
More a definition rather than a technique, simply means that the package-todie area ratio is not bigger than 1,2.



Low cost and low profile

COB (Chip On Board)

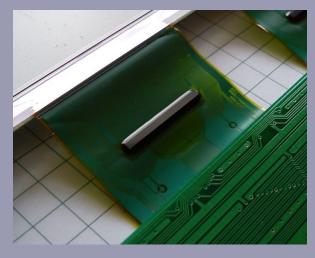
• Cheap devices (clocks, calculators)



FCOB (Flipped Chip on Board)

• SO-DIMM memories, Mobile phones

COF (Chip On Flex)LCD drivers





MCM (Multi-Chip Module)

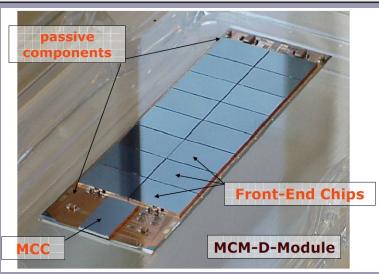
Several dies mounted on the same substrate to provide a finished module.

- good integration
- better electrical performances (like short propagation delay)
- MCM-C and MCM-D are inherited from hybrid technology.

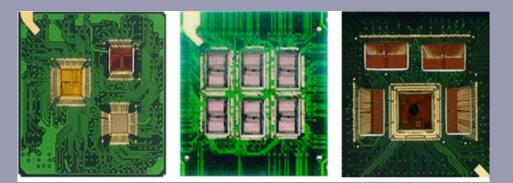
Technology	Support	Process	Spacing/ Width
MCM-D (Deposited)	Alumina, BeO	photolithographic	20um
MCM-C (Ceramic)	Co-fired ceramic	printing	50um
MCM-L (Laminate)	Organic laminate	HD PCB	75um
MCM-S (Silicon) *	Silicon	foundry process	<10um

* MCM-S never managed to be a very succesful technology itself.

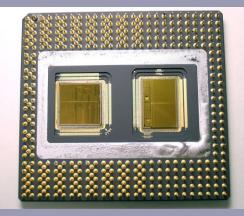
MCM examples



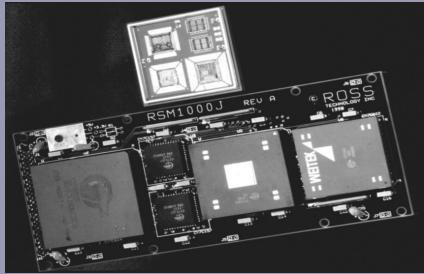
MCM-D (Atlas experiment)



MCM-L (Amkor)



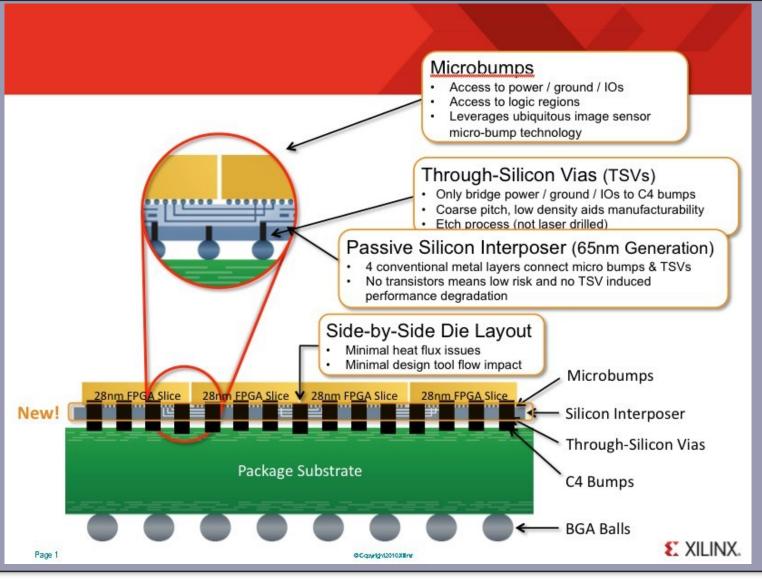
MCM-C (Pentium Pro)



MCM vs Single die package

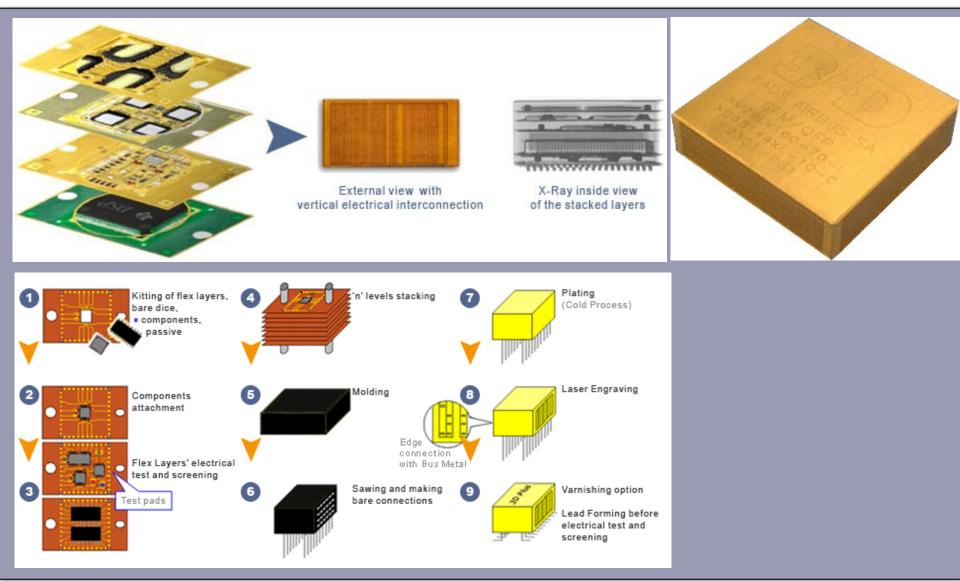
Multi-Chip Modules

Xilinx Virtex 7 = State of the Art MCM



Multi-Chip Modules

MCM stacked in 3D (3D Plus)



Multi-Chip Modules

KGD (Known Good Die)

KGD is an important concept for multiple dies assemblies (MCM,COB,SiP).

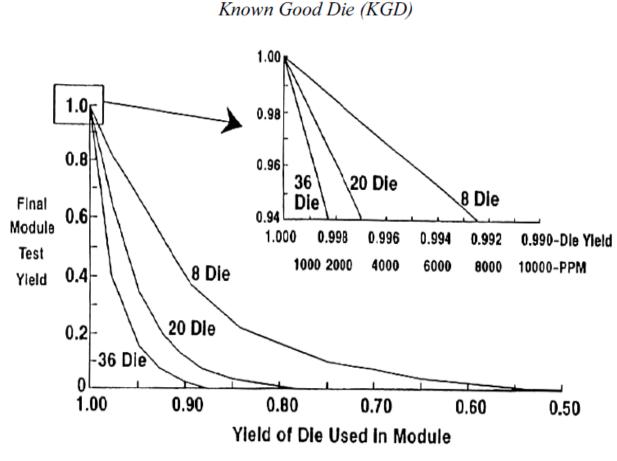


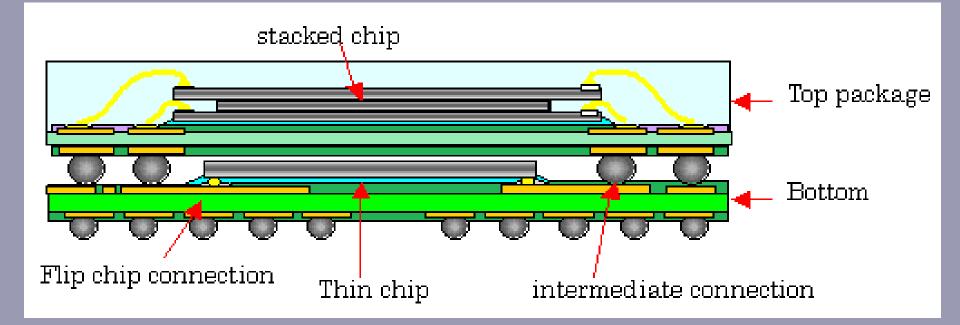
Figure 6-5. Multichip Assembly/Electrical Yield vs. Electrical Yield of Die

85

SiP (System in Package)

A SiP is an assembly of multiple elements (dies, sensors, passives...) <u>of different</u> <u>technologies</u>.

It envoles very advanced techniques like die stacking, PoP (package on package), short wire-bonding, thin wafers, silicon interposers...



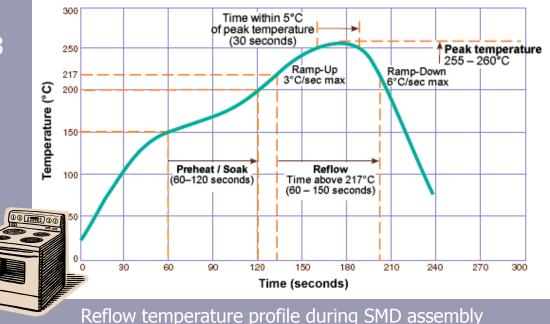
CTE (Coefficient of Thermal Expansion).

In a package, we have to choose materials with compatible CTE.

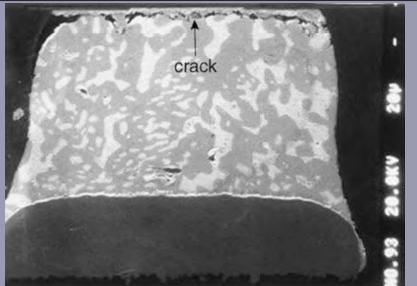
Material	CTE (ppm/K)	Young Modulus (GPa)	Thermal conductivity (W/(m.K))
Copper	17	119	398
Silicon	3	131	157
Mold compound	12-27	18	0.6
Alumina	6.5	25	25
PCB material	15-17	11	25

During operation but also during the assembly materials expand in 3 dimensions with temperature.

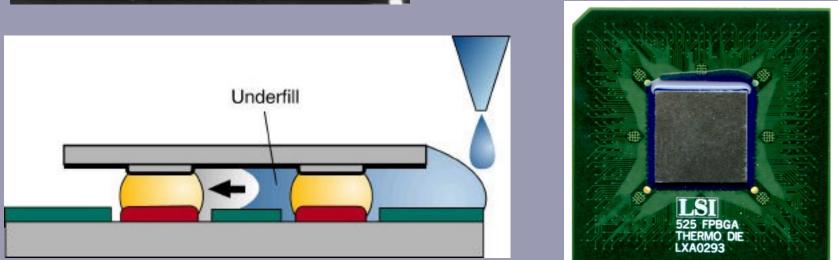
In large BGA packages, the balls in the corners are sometimes nCTF (non Critical To Function) because they have more constraints and a big chance to fail.



Underfill

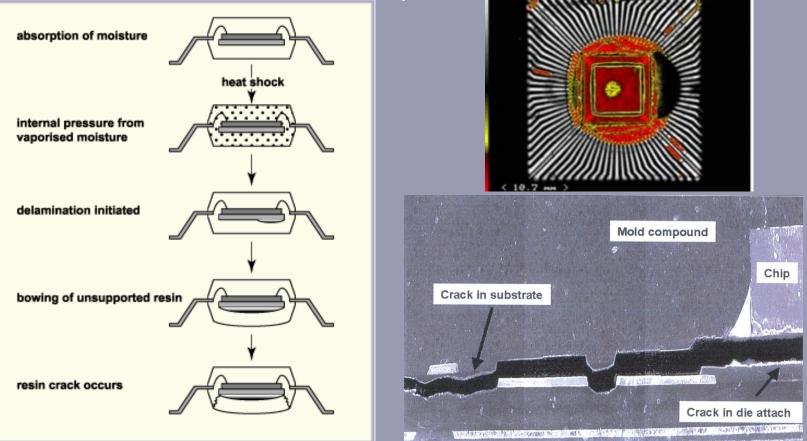


- CTE mismatch is a big problem for flipchip assembly, the thermo-mechanical stress breaks solder bumps.
- The solution is to add some underfill between the die and the substrate.
- Underfill resins are loaded with silica and have CTE around 30ppm / K



Moisture : popcorn effect

Absorbed moisture in non-hermetic packages (mostly plastic) creates the "Popcorn effect" during assembly.



Bake critical components (check MSL) and PCB before assembly.

Technical aspects

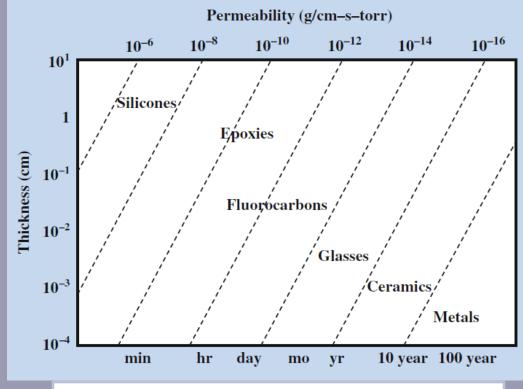
Hermetic package

- Moisture and contamination are major sources of reliability issues.
- Plastic packages are not hermetic so for critical applications ceramic or glass/metal should be used.

<u>But</u> do not seal an hermetic package with moisture or contamination already inside ...



Hermetic QFN with ceramic package and sealed Kovar cover

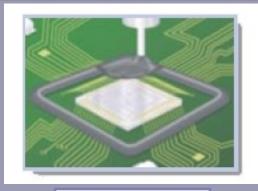


Time to reach 50% of the external humidity

Technical aspects

Encapsulation resins - Coating

- Dam & Fill
 - It's an alternative to molding for low volumes. Dam is done first with high viscosity fluid and then Fill.
 - Can build custom shapes
- Glop Top
 - Single drop of resin.
 - Round shape.
- Hybrids and MCM are often protected by coating products (organic + mineral) to have mechanical and moisture protection.
- A 25 um aluminum wire has a typical bond strength of 3 to 5.5 grams. A 12 um thick coating of Parylene increases that strength to 40 grams.

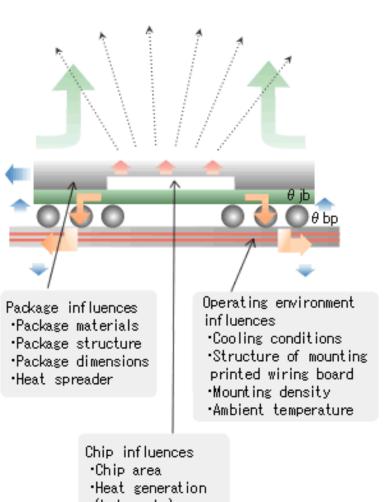




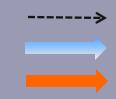


Glop Top

Heat dissipation



- Heat Radiation 1.
- 2. Convection
- 3. Conduction

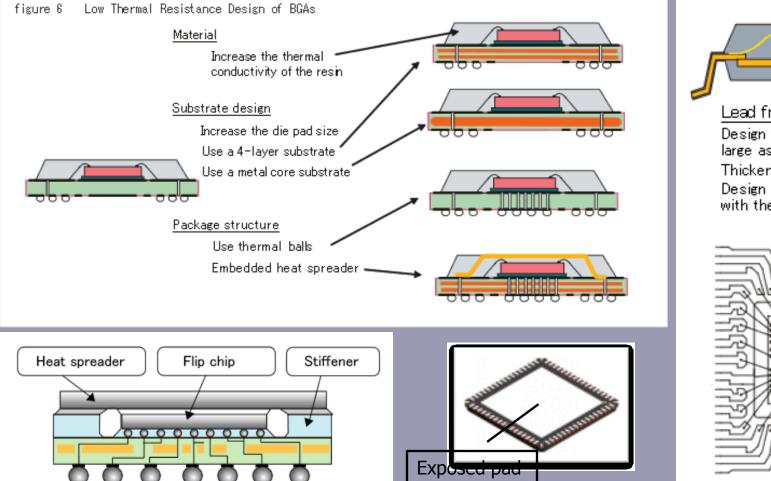


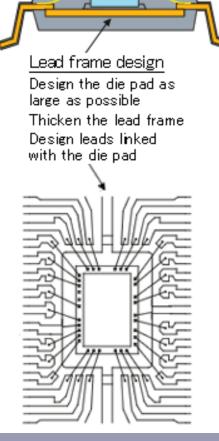
Thermal simulation for a 400 pins FCBGA (CERN) :

- Heat dissipated from PCB (%) 86.6
- Heat dissipated from package top (%) 1.4
- Heat dissipated from others (%) 12.0

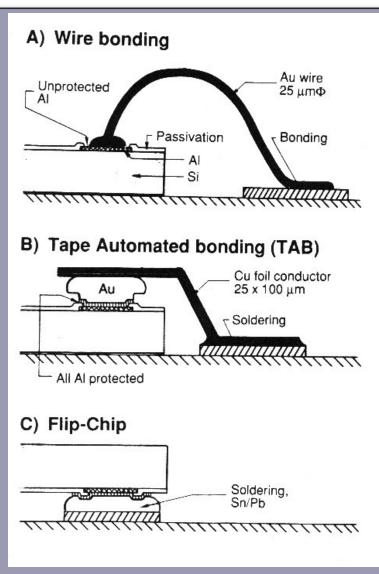
(hot spots) Power consumption

Heat dissipation techniques





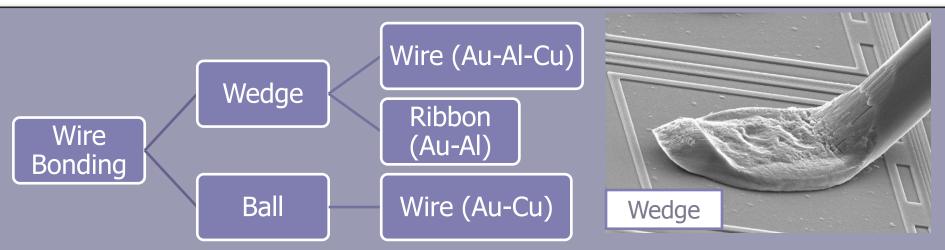
Electrical connections



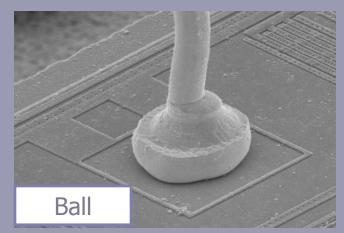
	WB	Flip-chip	ТАВ
Signal Integrity		-	
Flexibilty	+		-
Density	+	++	-
Production in 2010	85% ?	13%	2% ?
Cost (for low volumes)	+	- (NRE)	- (NRE)

	PGA with WB	BGA with FC		
Inductance	19.6 nH	7.9 nH		
Capacitance	15.9 pF	6.2 pF		
Resistance	21 Ω	2.1 Ω		
Propagation delay	946 ps	243 ps		
Flip-chip vs wire bonding				

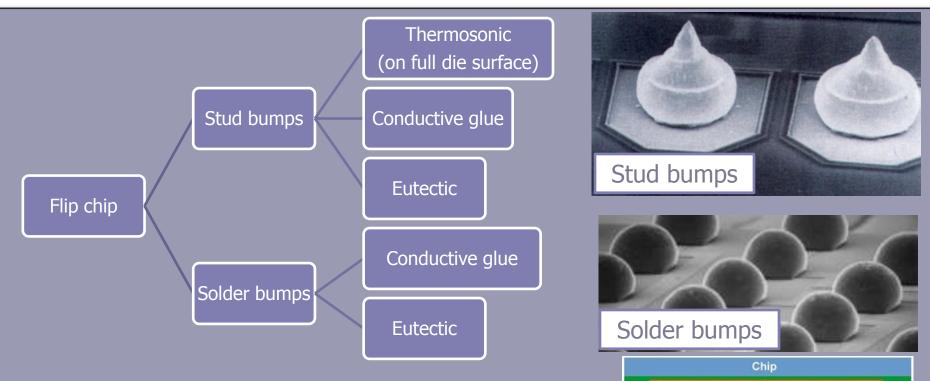
Electrical connections : Wire bonding



- Copper and gold need additional heat (130 °C).
- Industry uses mainly copper ball bonding but starts to replace gold by copper (cheaper).
- Wedge bonding is directional (angle <45°).
- Ribbon is suitable for power or RF applications (small R and L) but can be replaced by multiple wires connections.



Electrical connections : flip-chip

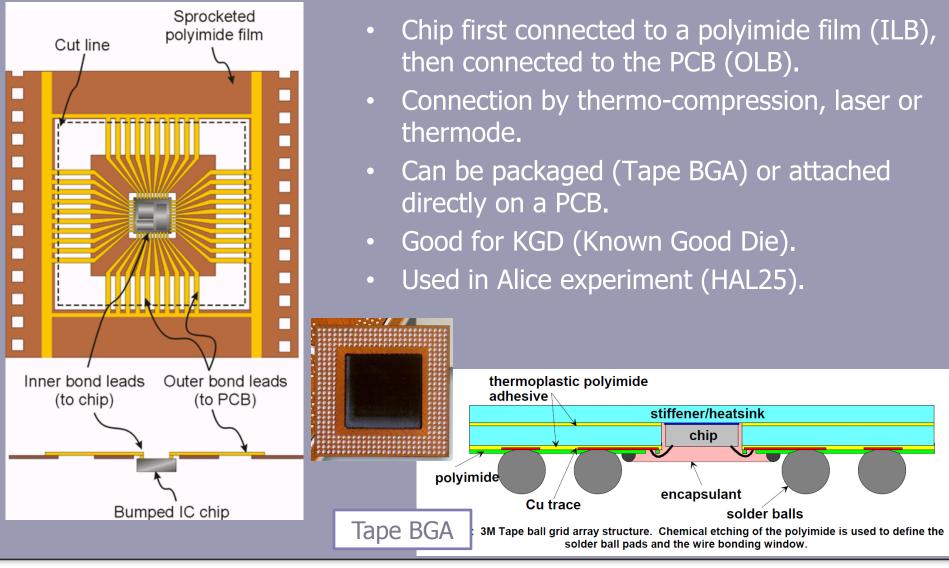


- For solder bumps it's necessary to insert an « Under Bump Metalisation » (UBM) to provide a solderable interface on the pad.
- Fusion temperature of solder bumps is higher than in a standard electronic assembly process.

Cu_eSn₅

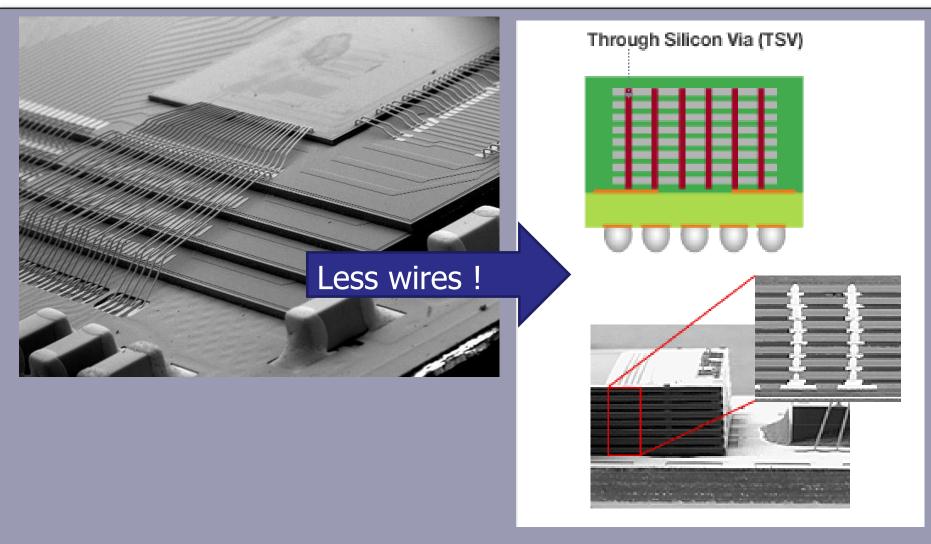
Ni Cu Substrate

TAB (Tape Automated bonding)



Technical aspects

TSV (Through-Silicon Via)



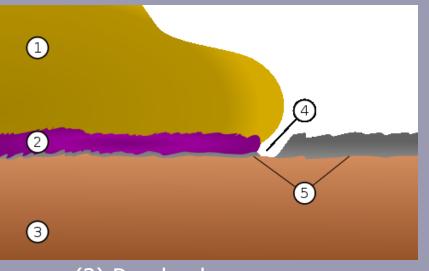
Failures : intermetallics

• « Purple plague » or Kirkendall effect with Au bonding wire over Al pad.

Caused by moisture + high temperature
+ ionic contamination on bonding pads.

 Can be solved by changing the bonding process from thermocompression (400 °C) to thermosonic (100 °C) bonding.

• Intermetallics can be also an issue in flip-chip assemblies.



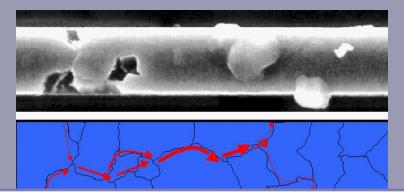
(2) Purple plague(5) Chip aluminum contact

Failures : electromigration

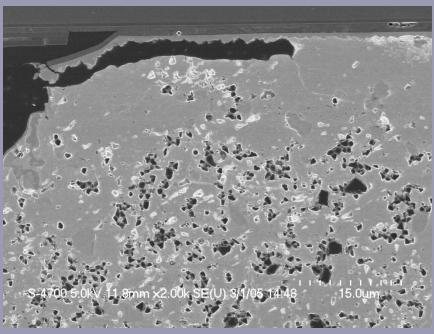
• Transport of material in a conductor due to the current density (current to cross section ratio) and the temperature.

• Electromigration is well know from ASIC designers but it appears to be a new problem for package reliability.

• ROHS forces people to re-evaluate the phenomena for packaging.



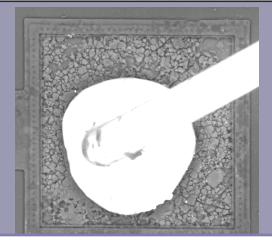
Electromigration in aluminium conductor



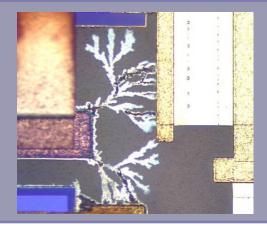
Electromigration in solder bumps

Other failures

- Corrosion is harmful for conductors : bonding pads, bondwires,UBM, bond wires. There are many sources:
 - moisture (from outside or trapped)
 - solder flux solvents (flip-chip)
 - hydrogen outgassing
- Tin whiskers on leads outside the package.
- Dendrite growth, due to ionic contamination + moisture + voltage bias.
- Wire bonds mechanical resonance (if no encapsulation) : a 1mm long 25um wire resonates at 30khz (gold) or 80 khz (aluminum).



Corrosion on a bond pad



Sliver dendrite from conductive epoxy glue

Conclusion

- IC packaging is a mixed of many disciplines : materials science, mechanical and chemical engineering and almost no electronic.
- Reliability is a very important parameter, mainly based on experience.
- Embedded electronic and MEMS forced packaging engineers to innovate a lot but it's still a bottleneck. R&D is focused now on 3D packaging and cooling.

Short bibliography:

- "Integrated Circuit Packaging, Assembly and Interconnections" William J. Greig
- "Wire Bonding in Microelectronics 3rd edition" George Harman
- "Miniaturisation MCM & Packaging en Electronique et micro-electronique" Alexandre Val